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CORP
TOSHIBA CORP

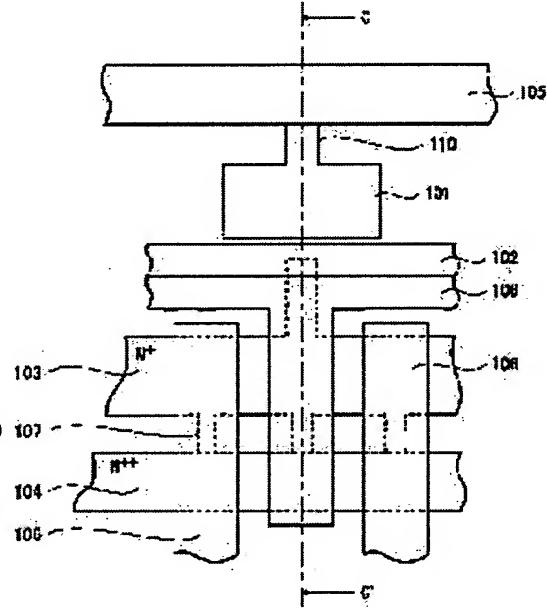
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(54) SOLID-STATE IMAGE PICKUP DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To solve the problem that charges of at least the amount of saturation charge are discharged to a first OFD 104, or in a picture element, charges of at least the amount of saturation charge are discharged to an adjacent second OFD, after charges are transferred to a CCD shift register, in the conventional case, but an OFD barrier part for deciding the amount of saturation is formed by an ion implantation process of impurities, so that a manufacturing process for forming the barrier part is increased.

SOLUTION: The potential barrier part is formed in such a manner that a first OFD barrier 107 and a second OFD barrier 110 obtain narrow channel effect, thereby enabling reduction of ion implantation process for forming the potential barrier part and reduction of manufacturing cost.



LEGAL STATUS

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